

Change in the parameters of electron-irradiated 4H-SiC schottky diodes as a function of the time during low-temperature isothermal annealing

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Comparative investigation of the graphene-on-silicon carbide and CVD graphene as a basis for biosensor application

Sleptsuk, Natalja; Lebedev, Alexander A.; Eliseyev, Ilya; **Korolkov, Oleg; Toompuu, Jana; Land, Raul; Mikli, Valdek;** Zubov, Alexander; **Rang, Toomas** Modern Materials and Manufacturing 2019 : 12th International DAAAM Baltic Conference and 27th International Baltic Conference BALTMATRIB 2019. Selected, peer reviewed papers from the conference Modern Materials and Manufacturing 2019 (MMM 2019), April 24-26, 2019, Tallinn, Estonia 2019 / p. 185-190 : ill https://www.ester.ee/record=b5235278*est <https://www.scientific.net/KEM.799.185> <https://doi.org/10.4028/www.scientific.net/KEM.799.185> [Conference proceeding at Scopus](#) [Article at Scopus](#)

Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons

Kozlovski, Vitali V.; **Korolkov, Oleg;** Lebedev, Alexander A.; **Toompuu, Jana; Sleptsuk, Natalja** Silicon Carbide and Related Materials 2019 : 18th International Conference on Silicon Carbide and Related Materials 2019 (ICSCRM 2019), Kyoto, Japan, September 29 - October 4, 2019 2020 / p. 231-236 <https://doi.org/10.4028/www.scientific.net/MSF.1004.231> [Conference Proceedings at Scopus](#) [Article at Scopus](#)

Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0.9 MeV electrons

Lebedev, Alexander A.; Davidovskaja, Klavdia; Kozlovski, Vitali V.; **Korolkov, Oleg; Sleptsuk, Natalja; Toompuu, Jana** Silicon Carbide and Related Materials 2016 : selected, peer reviewed papers from the 11th European Conference on Silicon Carbide and Related Materials 2016 (ECSCRM 2016), September 25-29, 2016, Halkidiki, Greece 2017 / p. 447-450 : ill <https://doi.org/10.4028/www.scientific.net/MSF.897.447>

Degradation of 600-V 4H-SiC Schottky diodes under irradiation with 0,9 MeV electrons

Lebedev, Alexander A.; Davydovskaja, K. S.; Kozlovski, Vitali V.; **Korolkov, Oleg; Sleptsuk, Natalja; Toompuu, Jana** 11th European Conference on Silicon Carbide and Related Materials : September 25-29, 2016, Porto Carras Grand Resort, Halkidiki, Greece : [poster session] 2016 / p. 49

Dependence of the carrier removal rate in 4H-SiC PN structures on irradiation temperature

Lebedev, Alexander A.; Davydovskaya, Klavdia S.; Kozlovski, Vitali V.; **Korolkov, Oleg; Sleptsuk, Natalja; Toompuu, Jana** Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018, Birmingham, UK 2019 / p. 730-733 <https://doi.org/10.4028/www.scientific.net/MSF.963.730> [Conference proceeding at Scopus](#) [Article at Scopus](#)

Influence of the proton irradiation temperature on the characteristics of high-power high-voltage silicon carbide schottky diodes

Kozlovski, Vitali V.; **Korolkov, Oleg;** Davydovskaya, Klavdia S.; Lebedev, Alexander A.; Levinshtein, Michael E.; **Sleptsuk, Natalja;** Strel'Chuk, Anatolii M.; **Toompuu, Jana** Technical Physics Letter 2020 / p. 287 - 289 <https://doi.org/10.1134/S1063785020030244> [Journal metrics at Scopus](#) [Article at Scopus](#) [Journal metrics at WOS](#) [Article at WOS](#)

Investigation of the graphene-on-silicon-carbide and CVD graphene as a basis for bioimpedance sensor applications : poster

Sleptsuk, Natalja; Land, Raul; Toompuu, Jana; Lebedev, Alexander A.; Davydov, Valery; Eliseyev, Ilya; Kalinina, Evgenia; **Korolkov, Oleg; Rang, Toomas** ePosters 2018 / 1 p.: ill <https://cdn.technologynetworks.com/ep/pdfs/natalja-sleptsuk-a-raul-land-a-jana-toompuu-a-alexander-lebedev-b-valery-davydov-b-ilya-eliseyev-b.pdf>

Low-temperature annealing of lightly doped n-4H-SiC layers after irradiation with fast electrons

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SiC schottky diode rectifier bridge represented as the diffusion-welded stack

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